

isc N-Channel MOSFET Transistor

2SK954

DESCRIPTION

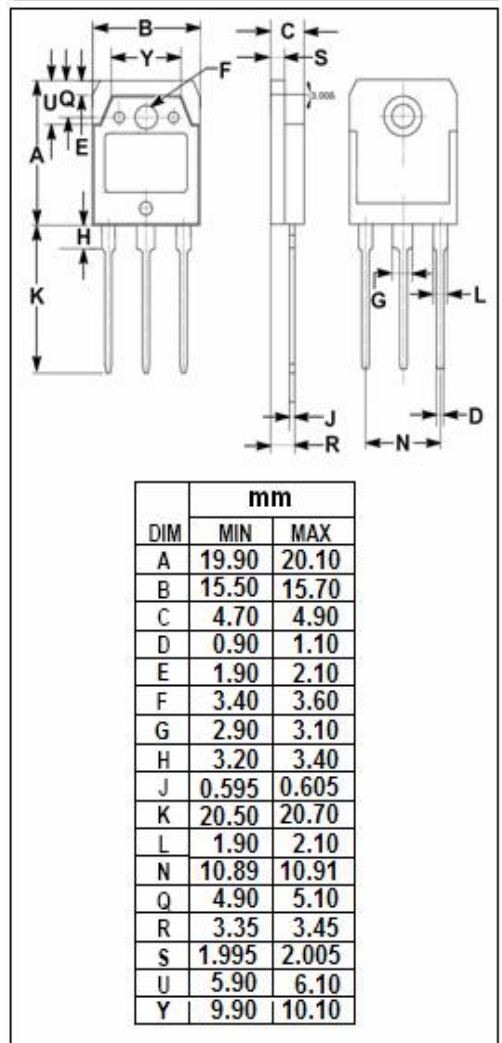
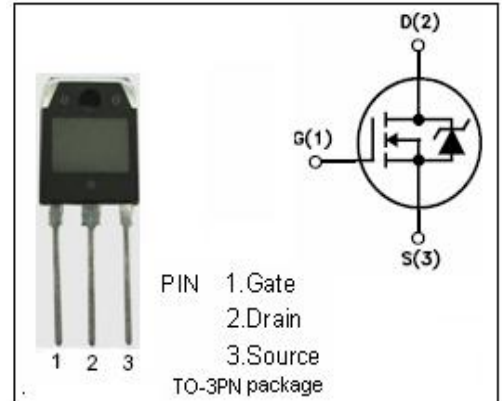
- Drain Current $-I_D=3A @ T_C=25^\circ C$
- Drain Source Voltage-
: $V_{DSS}=800V(\text{Min})$
- Fast Switching Speed

APPLICATIONS

- Designed especially for high voltage.
- high speed power switching.

ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ C$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{DSS}	Drain-Source Voltage ($V_{GS}=0$)	800	V
V_{GS}	Gate-Source Voltage	± 20	V
I_D	Drain Current-continuous@ $T_C=25^\circ C$	3	A
P_{tot}	Total Dissipation@ $T_C=25^\circ C$	100	W
T_j	Max. Operating Junction Temperature	80	$^\circ C$
T_{stg}	Storage Temperature Range	-55~150	$^\circ C$



isc N-Channel MOSFET Transistor**2SK954****• ELECTRICAL CHARACTERISTICS (T_C=25°C)**

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} =0; I _D = 10mA	800			V
V _{GS(TH)}	Gate Threshold Voltage	V _{DS} = V _{GS} ; I _D = 10mA	2.1	3.0	4.0	V
R _{DS(ON)}	Drain-Source On-stage Resistance	V _{GS} = 10V; I _D =1.5A		3.0	4.0	Ω
I _{GSS}	Gate Source Leakage Current	V _{GS} = ±20V; V _{DS} = 0			±100	nA
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =800V; V _{GS} = 0			500	uA
ton	Turn-on time	V _{GS} =10V; I _D =2.1A;		60	90	ns
toff	Turn-off time	R _L =50 Ω		210	340	ns
V _{SD}	Diode Forward Voltage	I _F =3A; V _{GS} =0		1.00	1.35	V